

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(e))

Docket No.  
YOR920030541US1  
(17113)

In Re Application Of: **Harold J. Hovel, et al.**

Serial No.  
10/696,632

Filing Date  
October 29, 2003

Examiner  
Unassigned

Group Art Unit  
Unassigned

Title: **SINGLE AND DOUBLE-GATE PSEUDO-FET DEVICES FOR SEMICONDUCTOR MATERIALS  
EVALUATION**

Address to:  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

**37 CFR 1.97(c)**

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

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**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0510/IBM**  
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- ☐ Charge the amount of \_\_\_\_\_
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William C. Roch  
Signature

Dated: **January 14, 2004**

William C. Roch, Esq.  
Reg. No. 24,972

Correspondence Address  
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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**



**Applicant:** Harold J. Hovel, et al

**Examiner:** Unassigned

**Serial No.:** 10/696,632

**Group Art Unit:** Unassigned

**Filed:** October 29, 2003

**Docket:** YOR920030541US1 (17113)

**For:** SINGLE AND DOUBLE-GATE PSEUDO-FET DEVICES FOR SEMICONDUCTOR MATERIALS EVALUATION

**Dated:** January 14, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

This Information Disclosure Statement is being filed in accordance with 37 C.F.R. §§ 1.97 (b), within three months of the filing of the subject patent application, to provide copies of the references cited and discussed on pages 2-4, while noting that U.S. Patent Application Serial No. 09/770,955, cited on page 2, has issued as U.S. Patent 6,429,145, copy enclosed.

Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

Respectfully submitted,

William C. Roch

Registration No.: 24,972

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**CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

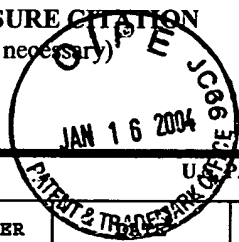
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William C. Roch

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**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)



Docket Number (Optional)  
YOR920030541US1 (17113)

Application Number  
10/696,632

Applicant(s)  
Harold J. Hovel, et al.

Filing Date  
October 29, 2003

Group Art Unit  
Unassigned

**UNITED STATES PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,429,145 B1	8/6/02	Hovel			

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	"Temperature And Magnetic Field Dependence Of The Carrier Mobility In SOI-Wafers By The Pseudo-MOSFET Method," Electrochemical Society Proceedings, by C. Rossel, et al., pp. 479-486
	"Si Film Electrical Characterization in SOI Substrates by the HgFET Technique," Solid State Electronics, by H.J. Hovel pp. 1311-1333, 2003
	"Extremely Low Resistivity Erbium Ohmic Contacts To n-type Silicon," Physics Letters, by P.L. Janega, et al., pp. 1415-1417
	"The Schottky-barrier Height Of The Contacts Between Some Rare-earth Metals (and silicides) And p-type Silicon," 1981 American Institute of Physics, by H. Norde, et al., pp. 865-867

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.